

# AOS Semiconductor Product Reliability Report

## AOD466/AOD466L, rev A

**Plastic Encapsulated Device** 

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This AOS product reliability report summarizes the qualification result for AOD466. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOD466 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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#### I. Product Description:

The AOD466 uses advanced trench technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications. Standard Product AOD466 is Pb-free (meets ROHS & Sony 259 specifications). AOD466L is a Green Product ordering option. AOD466 and AOD466L are electrically identical.

Absolute Maximum Ratings T <sub>A</sub> =25°C unless otherwise noted						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage	Drain-Source Voltage		25	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
Continuous Drain T <sub>A</sub> =25°C			30			
Current	T <sub>A</sub> =100°C	I <sub>D</sub>	25	Α		
Pulsed Drain Current		I <sub>DM</sub>	70			
Avalanche Current		I <sub>AR</sub>	20	А		
T <sub>A</sub> =25°C		PD	30	w		
Power Dissipation	T <sub>A</sub> =100°C	ГД	15	vv		
	T <sub>A</sub> =25°C	P <sub>DSM</sub>	2.5	w		
Power Dissipation	T <sub>A</sub> =70°C	F DSM	1.6	vv		
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 175	°C		

Thermal Characteristics					
Parameter	Symbol	Тур	Max	Units	
Maximum Junction-to- Ambient	T ≤ 10s	D	15	20	°C/W
Maximum Junction-to- Ambient	Steady- State	- R <sub>θJA</sub>	41	50	°C/W
Maximum Junction-to-Lead	Steady- State	$R_{ ext{ hetaJL}}$	3.6	5	°C/W



## II. Die / Package Information:

Process	AOD466 Standard sub-micron low voltage N channel process	AOD466L (Green Compound) Standard sub-micron low voltage N channel process
Package Type	3 leads TO252	3 leads TO252
Lead Frame	Cu L/F, Ni pad	Cu L/F, Ni pad
Die Attach	Soft solder	Soft solder
Bond wire	Al, 5mils and 12mils	AI, 5mils and 12mils
Mold Material	Soft solder	Soft solder
Filler % (Spherical/Flake)	90/10	100/0
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1*

Note \* based on info provided by assembler and mold compound supplier

## III. Result of Reliability Stress for AOD466 (Standard) & AOD466L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°c Green: 168hr 85°c /85%RH +3 cycle reflow@260°c	Ohr	Standard: 40 lots Green: 3 lots	6710pcs	0
HTGB	Temp = 150°c, Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82pcs 77+5 pcs / lot	0
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82pcs 77+5 pcs / lot	0
HAST	130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard : 40 lots Green: 3 lots (Note B**)	2365pcs 50+5 pcs / lot	0
Pressure Pot	121°c , 15+/-1 PSIG, RH=100%	96 hrs	Standard : 33 lots Green: 3 lots (Note B**)	1980pcs 50+5 pcs / lot	0
Temperature Cycle	-65°c to 150°c , air to air,	250 / 500 cycles	Standard : 40 lots Green: 3 lots (Note B**)	2365pcs 50+5 pcs / lot	0



Internal Vision	NA	5	5	0
Cross-section		5	5	
X-ray		5	5	
	NA	5	5	0
Room Temp	0hr	40	40 wires	0
150°c bake	250hr	40	40 wires	
150°c bake	500hr	40	40 wires	
230°c	5 sec	15	15 leads	0
150°c	0hr	10	10	0
	Cross-section X-ray Room Temp 150°c bake 150°c bake 230°c	Cross-section X-rayNARoom Temp 150°c bake 150°c bakeOhr 250hr 500hr230°c5 sec	Cross-section X-ray5NA5Room Temp 150°c bake0hr 250hr150°c bake250hr 500hr230°c5 sec	Cross-section X-ray55NA55NA55Room Temp 150'c bake 150'c bake0hr 250hr40 40 40150'c bake 150'c bake250hr 500hr40 40230'c5 sec1515 leads

#### III. Result of Reliability Stress for AOD466 (Standard) & AOD466L (Green) Continues

**Note A:** The HTGB and HTRB reliability data presents total of available AOD466 and AOD466L burn-in data up to the published date.

**Note B:** The pressure pot, temperature cycle and HAST reliability data for AOD466 and AOD466L comes from the AOS generic package qualification data.

### **IV. Reliability Evaluation**

#### FIT rate (per billion): 128 MTTF = 891 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AOD466). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =  $\text{Chi}^2 \times 10^9 / [2 (\text{N}) (\text{H}) (\text{Af})] = 1.83 \times 10^9 / [2 (164) (168) (258)] = 128$ MTTF =  $10^9 / \text{FIT} = 7.81 \times 10^6 \text{hrs} = 891 \text{years}$ 

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval **N** = Total Number of units from HTRB and HTGB tests

**H** = Duration of HTRB/HTGB testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C) Acceleration Factor [**Af**] = **Exp** [Ea /  $\mathbf{k}$  (1/Tj u = 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** =The use junction temperature in degree (Kelvin), K = C+273.16

 $\mathbf{k}$  = Boltzmann's constant, 8.617164 X 10<sup>-5</sup> eV / K



## V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual. Guaranteed Outgoing Defect Rate: **< 25 ppm** Quality Sample Plan: conform to **Mil-Std-105D**